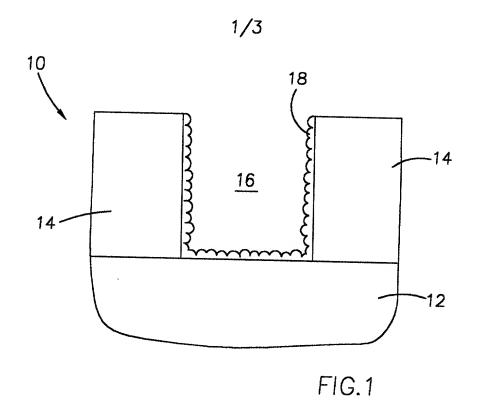
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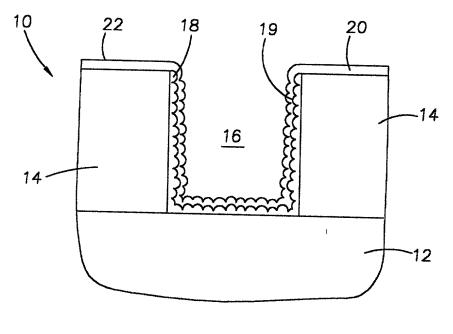


FIG.2

n A

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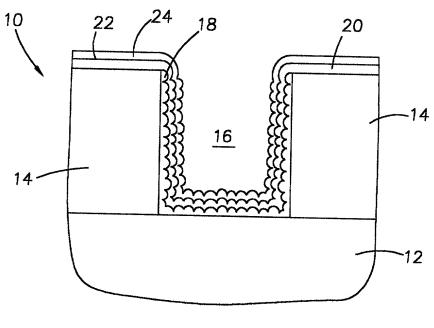


FIG.3

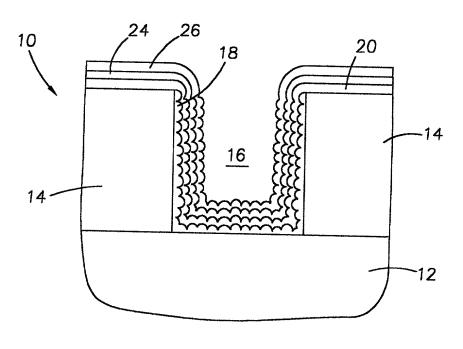


FIG.4

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